Pb Free Plating Product

MUR3060G

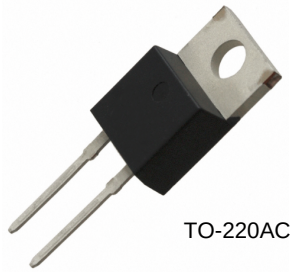
30 Ampere Single Glass Passivated Chip Ultrafast Recovery Rectifier Diode

Features

- Glass passivated chip junction EPI wafer
- Ultrafast recovery time for high efficiency
- Low reverse leakage current
- High surge capacity

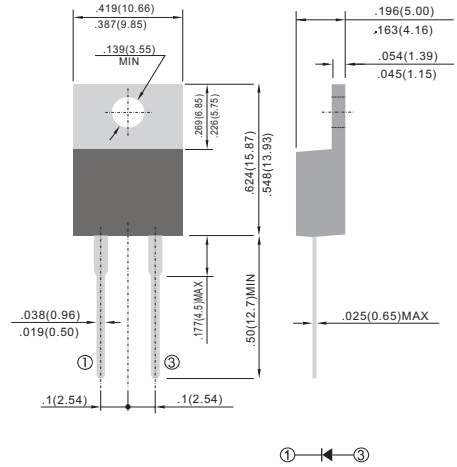
Mechanical Data

- Case: TO-220AC heatsink
- Terminals: Lead solderable per MIL-STD-202, Method 208
- Polarity: As marked
- Standard packaging: Any
- Weight: 2.5 gram approximately



TO-220AC Heatsink

TO-220AC Unit : inch (mm)



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Rating at 25°C ambient temperature unless otherwise specified.
Single phase, half wave, 60Hz, resistive or inductive load.
For capacitive load, derate current by 20%.

	SYMBOL	MUR3060G	UNIT
Maximum Recurrent Peak Reverse Voltage	V_{RRM}	600	V
Maximum RMS Voltage	V_{RMS}	420	V
Maximum DC Blocking Voltage	V_{DC}	600	V
Maximum Average Forward Rectified Current T_C=125°C	$I_{F(AV)}$	30.0	A
Peak Forward Surge Current, 8.3ms single Half sine-wave superimposed on rated load (JEDEC method)	I_{FSM}	250	A
Maximum Instantaneous Forward Voltage @ 30.0 A	V_F	1.7	V
Maximum DC Reverse Current @T_J=25°C At Rated DC Blocking Voltage @T_J=125°C	I_R	5.0 100	uA uA
Maximum Reverse Recovery Time (Note 1)	Trr	60	nS
Typical junction Capacitance (Note 2)	C_J	120	pF
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 to +150	°C

NOTES : (1) Reverse recovery test conditions I_F = 0.5A, I_R = 1.0A, Irr = 0.25A.

(2) Measured at 1.0 MHz and applied reverse voltage of 4.0 Volts DC.

FIG.1 - FORWARD CURRENT DERATING CURVE

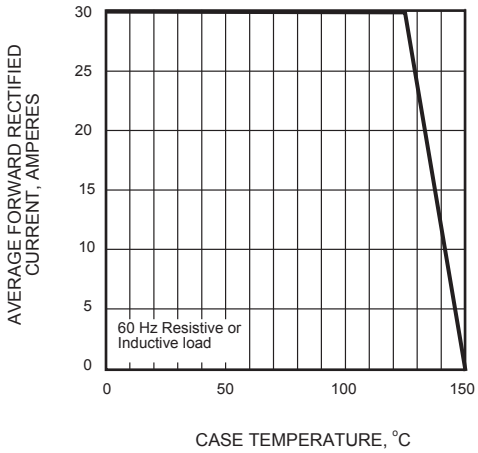


FIG.2 - MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT

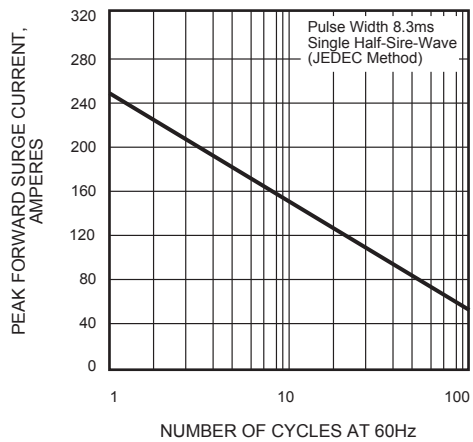


FIG.3 - TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS

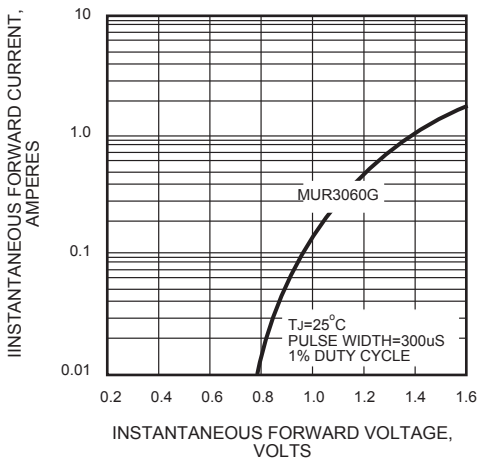


FIG.4 - TYPICAL REVERSE CHARACTERISTICS

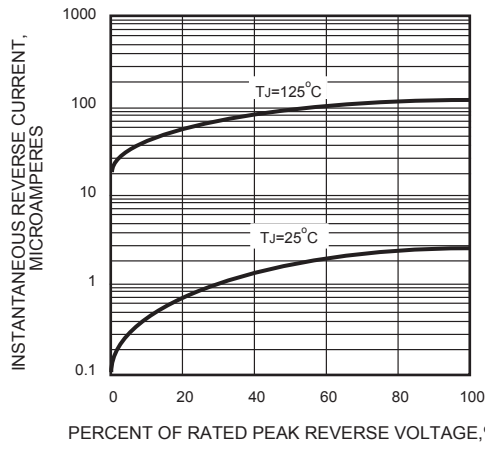


FIG.5 - TYPICAL JUNCTION CAPACITANCE